

36 EDS Members Elected to the IEEE Grade of Fellow Effective 1 January 2010

Joerg Appenzeller, Birck Nanotechnology Center, West Lafayette, IN, USA
for contributions to carbon nanotube transistors and circuits

Jennifer Bernhard, University of Illinois at Urbana-Champaign, Urbana, IL, USA
for development of multifunctional, reconfigurable, and integrated antennas

Sandoval Carneiro, Federal University of Rio De Janeiro, Rio De Janeiro, Brazil
for leadership in power systems research and engineering education

Amitava Chatterjee, Texas Instruments Inc., Dallas, TX, USA
for contributions to complementary metal oxide semiconductor device technology and on-chip electrostatic discharge protection

Mariesa Crow, Missouri University of Science & Technology, Rolla, MO, USA
for contributions to power engineering education and to computational methods for power system analysis

Paul Dodd, Sandia National Laboratories, Albuquerque, NM, USA
for contributions to the understanding and simulation of single-event effects in microelectronics

Long-Sheng Fan, National Tsing Hua University, San Jose, CA, USA
for contributions to Micro Electro-Mechanical Systems

Ian Ferguson, Georgia Institute of Technology, Atlanta, GA, USA
for the development of semiconductor materials and devices for infrared and ultraviolet sensor applications

Yogesh Gianchandani, University of Michigan, Ann Arbor, MI, USA
for contributions to silicon-based microactuators and on-chip microplasmas

Gennady Gildenblat, Arizona State University, Tempe, AZ, USA
for contributions to modeling of metal-oxide semiconductor field effect transistors

Charles Goldsmith, MEMtronics Corporation, Plano, TX, USA
for development of micro-electromechanical capacitive switches

Masashi Horiguchi, Renesas Technology Corp., Tokyo, Japan
for contributions to circuit technologies for high-density low-power memories

Dimitrios Ioannou, George Mason University, Fairfax, VA, USA
for contributions to reliability and characterization of silicon-on-insulator devices and materials

Mohammad Karim, Old Dominion University, Norfolk, VA, USA
for leadership in engineering education through creation of interdisciplinary programs

Takamaro Kikkawa, Hiroshima University, Hiroshima, Japan
for contributions to interconnect technologies for integrated circuits

Fanny Klett, Fraunhofer Institute Digital Media Technology, Ilmenau, Germany
for contributions to development and application of educational technologies

Rhee Jin Koo, Dongguk University, Seoul, Korea
for contributions to Gallium Arsenide, Microwave and Millimeter-wave Monolithic Integrated Circuits

Richard Lai, Northrop Grumman Aerospace Systems, Redondo Beach, CA, USA
for development and space-qualified insertion of millimeter-wave transistor and integrated-circuit technologies

Yusuf Leblebici, Swiss Federal Institute of Technology, Lausanne, Switzerland
for contributions to reliability and design techniques for integrated circuits and systems

Patrick Lenahan, Pennsylvania State University, University Park, PA, USA
for contributions to understanding of radiation damage and reliability of metal-oxide semiconductor devices

Chang Liu, Northwestern University, Evanston, IL, USA
for contributions to bio-inspired and polymer micro electro-mechanical systems

Rich Liu, Macronix International Co. Ltd., Hsinchu, Taiwan
for leadership in electron-beam mask writing, interconnects, and non-volatile technology development

Francisco Mena, University of Seville, Sevilla, Spain
for contributions to the analysis and physical understanding of planar structures, anisotropic media, and metamaterials

Kaizad Mistry, Intel Corporation, Hillsboro, OR, USA
for contributions to high performance complementary metal-oxide semiconductor technology and reliability

Arokia Nathan, University College London, London, UK
for contributions to thin film transistor technologies

Kwok Ng, Semiconductor Research Corp (SRC), Durham, NC, USA
for contributions to the optimization of intrinsic parasitics in metal-oxide semiconductor field-effect transistor design

Yasuhisa Omura, Kansai University, Osaka, Japan
for contributions of silicon on insulator devices technology, analysis, and modeling

Fan Ren, University of Florida, Gainesville, FL, USA
for contributions to processing technologies for compound semiconductor devices

Thomas Skotnicki, STMicroelectronics, Crolles, France
for contributions to development of metal-oxide semiconductor field effect transistor models and advanced semiconductor technologies

Jordi Sune, Universitat Autònoma de Barcelona, Barcelona, Spain
for contributions to the understanding of gate oxide failure and reliability methodology

Nobukazu Teranishi, Panasonic Corporation, Kyoto, Japan
for contribution to the development of charge-coupled device image sensors

Charles Weitzel, Mesa, AZ, USA
for contributions to compound semiconductor technology and microwave devices

Jinming (Jimmy) Xu, Brown University, Providence, RI, USA
for contributions to sensor materials and bio-nano electronics

Shumpei Yamazaki, Kanagawa, Japan
for contributions to, and leadership in the industrialization of non-volatile memory and thin film transistor technologies

Howard Yang, Montage Technology Co. Ltd., Shanghai, China
for leadership in mixed-signal integrated circuit design and manufacturing

Jian Zhao, Rutgers University, Piscataway, NJ, USA
for contributions to vertical silicon carbide devices and process technologies

Hiroshi Iwai
2009 EDS Fellows Chair
Tokyo Institute of Technology
Yokohama, Japan